

Features

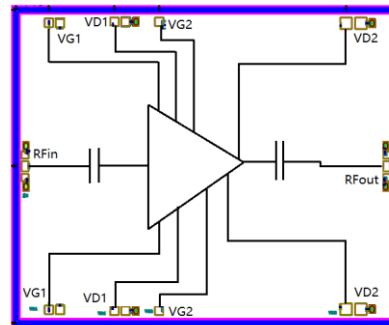
Gain: 26dB

Psat: 44dBm

Supply Current: 1130mA@+28V,-2.1V

Chip Size: 5100μm×4200μm

Functional Diagram



General Description

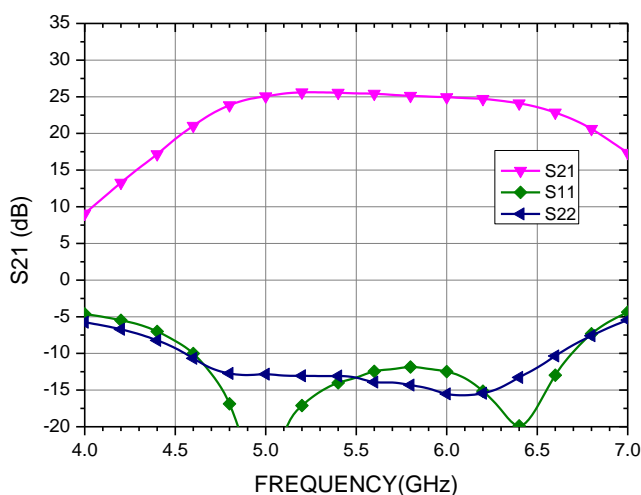
MWG801 is a power amplifier product designed and manufactured by GaN technology. This power amplifier can cover 5-6 GHz operating frequency band, using +28V voltage Vdd power supply, normal operating current 1130mA, providing 26 dB small signal gain, typical saturated output power up to 44 dBm.

Electrical Specification, TA = +25°C, Vdd=+28V, Vgg= -2.1V

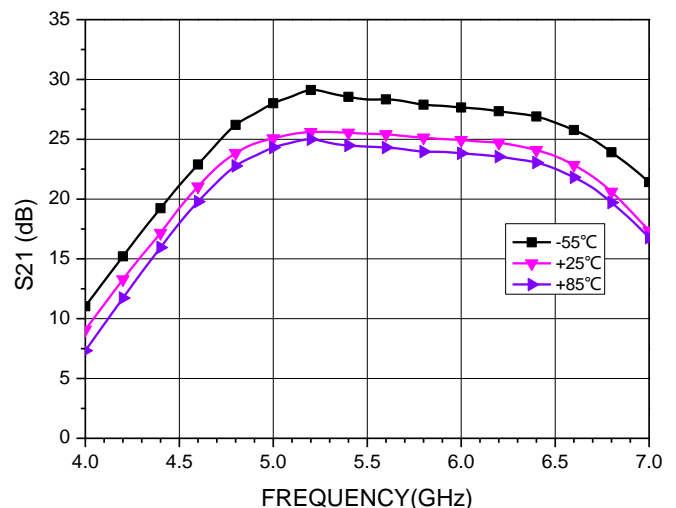
Parameter	Min	Typ	Max	Units
Bandwidth	5		6	GHz
Gain		26		dB
Input Return Loss		18		dB
Output Return Loss		14		dB
Saturation Output Power		44		dBm
Power Added Efficiency		30%		
Supply Current (@Vdd=28V,Vgg= -2.1V)		1130		mA

Test Results

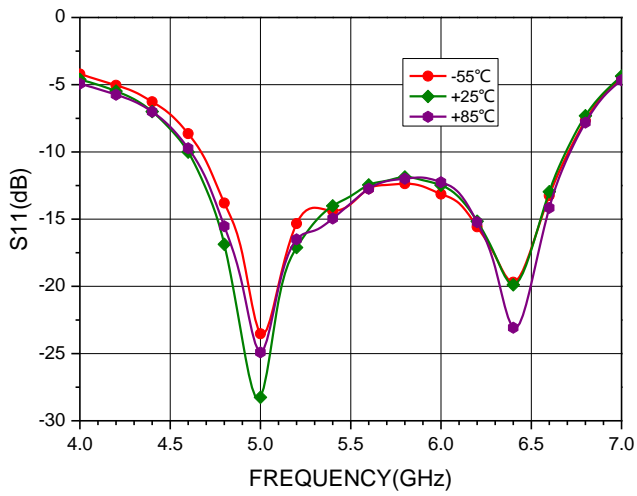
S_Parameter



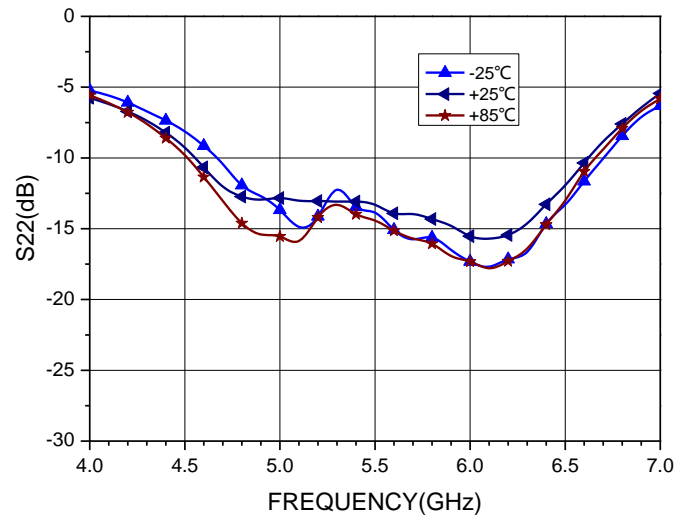
Gain



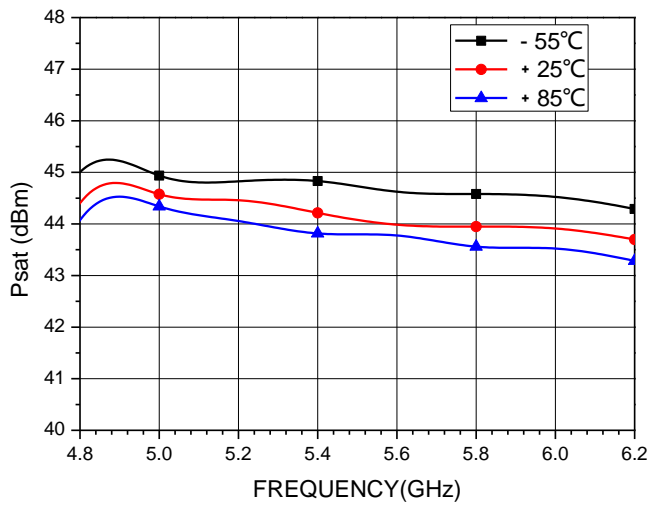
Input Return Loss



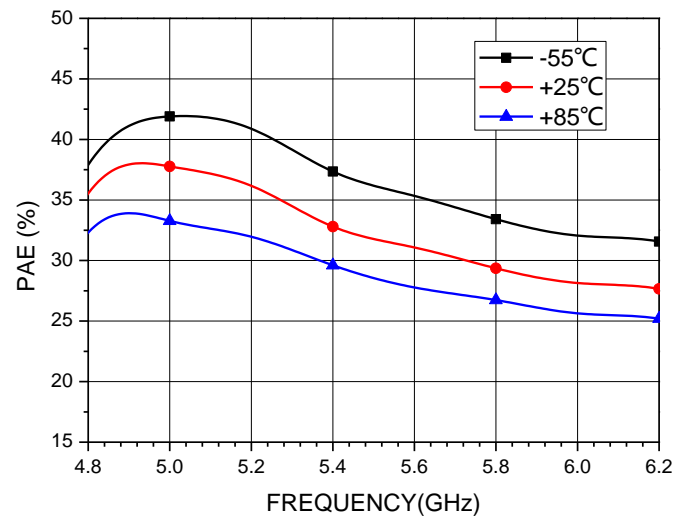
Output Return Loss



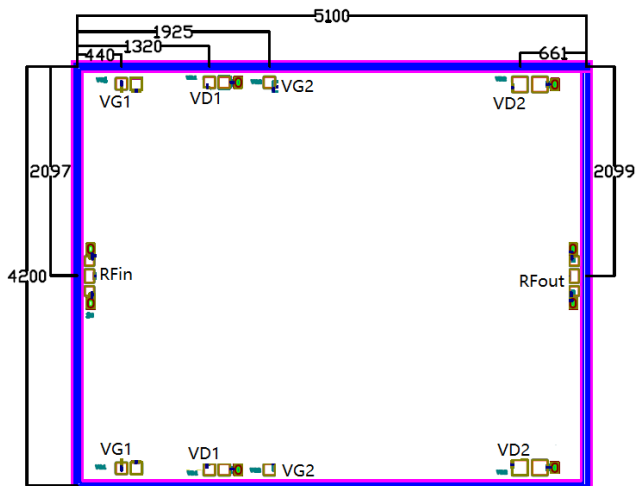
Psat



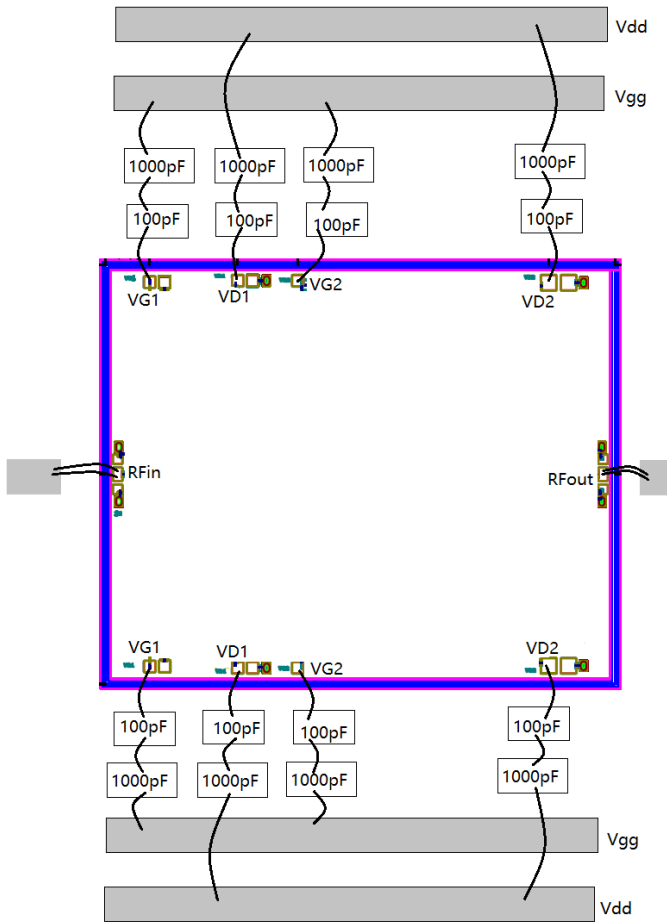
PAE



Chip Size



Assembly Diagram



Absolute Maximum Ratings

Voltage	+30V
RF Input Power	22dBm
Storage Temperature	-65 - +150°C
Operating Temperature	-55 - +85°C